# SILICON EPITAXIAL PLANAR SWITCHING DIODE

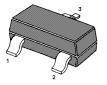
#### Features

- Small package
- Low forward voltage
- Fast reverse recovery time
- Small total capacitance

# Applications

• Ultra high speed switching application





Marking Code: **5D** SOT-23 Plastic Package

## Absolute Maximum Ratings (T<sub>a</sub> = 25 °C)

Parameter	Symbol	Value	Unit
Reverse Voltage	V <sub>R</sub>	70	V
Forward Current	I <sub>F</sub>	200	mA
Peak Forward Surge Current	I <sub>FSM</sub>	500	mA
Power Dissipation	P <sub>d</sub>	300	mW
Junction Temperature	Tj	150	°C
Storage Temperature Range	Ts	- 55 to + 150	°C

## Characteristics at T<sub>a</sub> = 25 °C

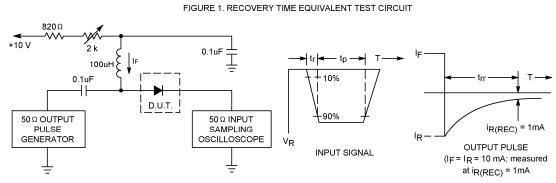
Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 1 \text{ mA}$ at $I_F = 100 \text{ mA}$	V <sub>F</sub>	0.55 0.85	0.7 1.1	V
Reverse Current at $V_R = 50 V$	I <sub>R</sub>	-	100	nA
Reverse Breakdown Voltage at $I_R = 100 \ \mu A$	V <sub>(BR)R</sub>	70	-	V
Diode Capacitance at $V_R = 0$ , f = 1 MHz	C <sub>T</sub>	-	2.5	pF
Reverse Recovery Time at $I_F = I_R = 10$ mA, $I_{R(REC)} = 1$ mA	t <sub>rr</sub>	-	4	ns



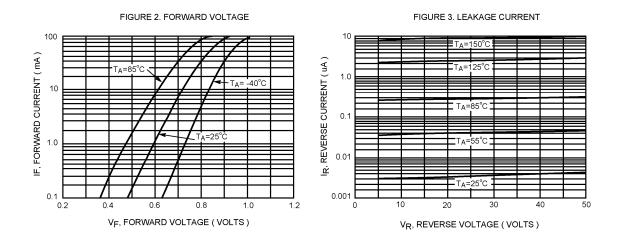
SEMTECH ELECTRONICS LTD. (Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)

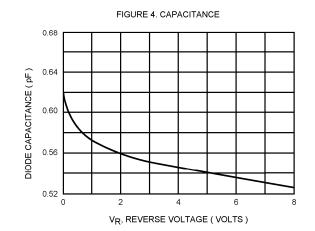


Dated : 10/10/2008



Notes: 1. A 2.0k  $_\Omega$  variable resistor adjusted for a Forward Current (IF) of 10mA. 2. Input pulse is adjusted so  $I_{R(peak)}$  is equal to 10mA. 3.  $t_p \gg t_{rr}$ 











Dated : 10/10/2008